MITSUBISHI ELECTRIC

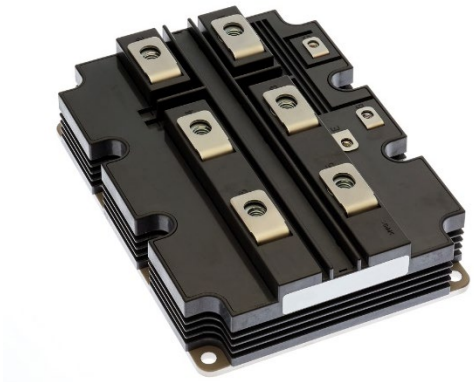
<High Voltage Insulated Gate Bipolar Transistor : HVIGBT >

CM1000HG-130XA

HIGH POWER SWITCHING USE
INSULATED TYPE

5th-Version HVIGBT (High Voltage Insulated Gate Bipolar Transistor) Modules

CM1000HG-130XA

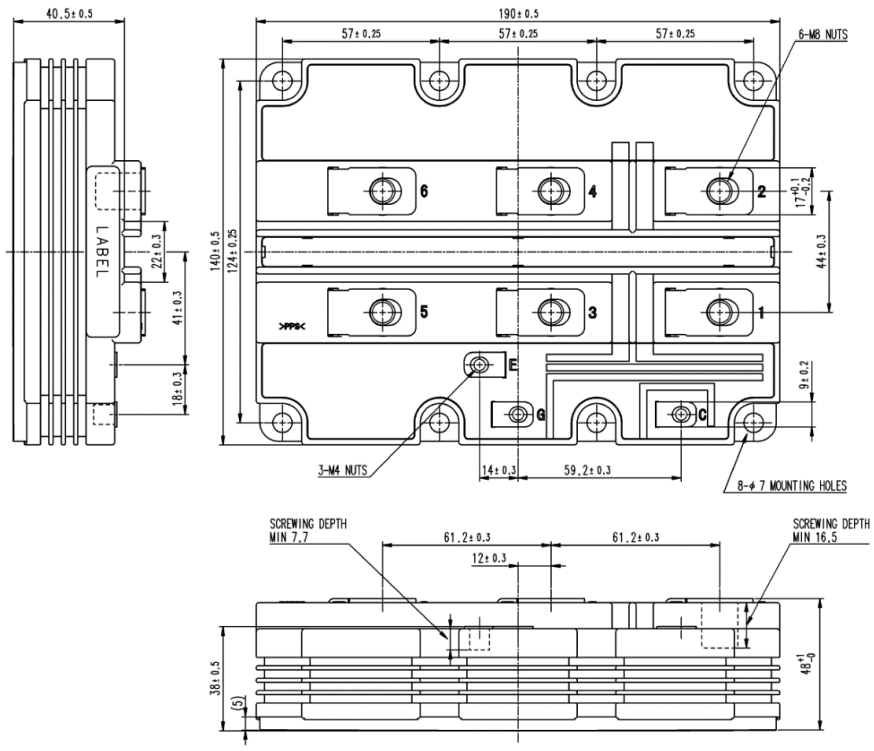


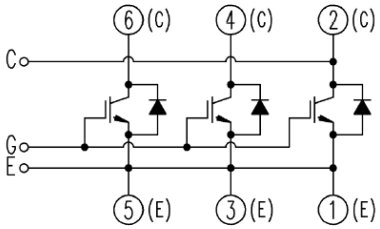
- I_C ..... 1000 A
- V_{CES} ..... 6500 V
- 1-element in Pack
- High Insulated Type
- CSTBT™(III) / RFC Diode
- AlSiC Baseplate
- UL recognized under UL1557

APPLICATION

Traction drives, High Reliability Converters / Inverters, DC choppers

OUTLINE DRAWING & CIRCUIT DIAGRAM **Dimensions in mm**





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CIRCUIT DIAGRAM

MAXIMUM RATINGS

Symbol	Item	Conditions	Ratings	Unit
V_{CES}	Collector-emitter voltage	V_{GE} = 0V, T_j = 150°C	6500	V
		V_{GE} = 0V, T_j =25°C	6300	
		V_{CE} = 0V, T_j = −50°C	5700	
V_{GES}	Gate-emitter voltage	V_{CE} = 0V, T_j = 25°C	± 20	V
I_C	Collector current	DC, T_C = 111°C	1000	A
I_{CRM}		Pulse (Note 1)	2000	A
I_E	Emitter current (Note 2)	DC, T_C = 95°C	1000	A
I_{ERM}		Pulse (Note 1)	2000	A
P_{tot}	Maximum power dissipation (Note 3)	T_c = 25°C, IGBT part	12500	W
V_{iso}	Isolation voltage	RMS, sinusoidal, f = 60Hz, t = 1min.	10200	V
Q_{PD}	Partial discharge	RMS, sinusoidal, f = 60Hz, V1 = 6900 V, V2 = 5100 V	10	pC
T_j	Junction temperature	—	−50 ~ +150	°C
T_{jop}	Operating junction temperature	—	−50 ~ +150	°C
T_{stg}	Storage temperature	—	−55 ~ +150	°C
t_{psc}	Short circuit pulse width	V_{CC} ≤ 4500V, V_{GE} = ±15V, $R_{G(on)}$ = 4.3Ω, $R_{G(off)}$ = 39Ω, Tj = 150°C	10	µs

ELECTRICAL CHARACTERISTICS

Symbol	Item	Conditions		Limits			Unit
				Min	Typ	Max	
I_{CES}	Collector cutoff current	V_{CE} = V_{CES}, V_{GE} = 0V	T_j = 25°C	—	—	5.0	mA
			T_j = 125°C	—	5.0	—	
			T_j = 150°C	—	—	150.0	
$V_{GE(th)}$	Gate-emitter threshold voltage	V_{CE} = 10V, I_C =100mA, T_j = 25°C		6.50	7.00	7.50	V
I_{GES}	Gate leakage current	V_{GE} = V_{GES}, V_{CE} = 0V, T_j = 25°C		-0.5	—	0.5	µA
C_{ies}	Input capacitance	V_{CE} = 10V, V_{GE} = 0V, f = 100kHz, T_j = 25°C		—	152	—	nF
C_{oes}	Output capacitance			—	6.2	—	nF
C_{res}	Reverse transfer capacitance			—	0.8	—	nF
Q_G	Total gate charge	V_{CC} = 3600V, I_C = 1000A, V_{GE} = ±15V		—	9.9	—	µC
V_{CEsat}	Collector-emitter saturation voltage	I_C =1000A (Note 4), V_{GE} = 15V	T_j = 25°C	—	2.60	—	V
			T_j = 125°C	—	3.25	—	
			T_j = 150°C	—	3.40	3.90	
$t_{d(on)}$	Turn-on delay time	V_{CC} = 3600V, I_C = 1000A, V_{GE} = ±15V, $R_{G(on)}$ = 4.3Ω, L_s = 150nH, Inductive load	T_j = 150°C	—	—	1.20	µs
t_r	Rise time		T_j = 150°C	—	—	070	µs
$E_{on(10\%)}$	Turn-on switching energy (per pulse) (Note 5)		T_j = 25°C	—	10.50	—	J
			T_j = 125°C	—	10.50	—	
			T_j = 150°C	—	10.50	—	
E_{on}	Turn-on switching energy (per pulse) (Note 6)		T_j = 25°C	—	11.00	—	J
			T_j = 125°C	—	11.00	—	
			T_j = 150°C	—	11.40	—	
$t_{d(off)}$	Turn-off delay time	V_{CC} = 3600V, I_C = 1000A, V_{GE} = ±15V, $R_{G(off)}$ = 39Ω, L_s = 150 nH, Inductive load	T_j = 25°C	—	7.40	—	µs
			T_j = 125°C	—	7.70	—	
			T_j = 150°C	—	8.00	—	
t_f	Fall time		T_j = 25°C	—	0.50	—	µs
			T_j = 125°C	—	0.60	—	
			T_j = 150°C	—	0.65	—	
$E_{off(10\%)}$	Turn-off switching energy (per pulse) (Note 5)		T_j = 25°C	—	5.50	—	J
			T_j = 125°C	—	7.10	—	
			T_j = 150°C	—	7.50	—	
E_{off}	Turn-off switching energy (per pulse) (Note 6)		T_j = 25°C	—	5.90	—	J
			T_j = 125°C	—	7.50	—	
			T_j = 150°C	—	8.00	—	

ELECTRICAL CHARACTERISTICS

Symbol	Item	Conditions		Limits			Unit
				Min	Typ	Max	
V_{EC}	Emitter-collector voltage (Note 2)	I_E = 1000A (Note 4), V_{GE} = 0V	T_j = 25°C	—	2.40	—	V
			T_j = 125°C	—	2.80	—	
			T_j = 150°C	—	2.90	3.40	
t_{rr}	Reverse recovery time (Note 2)	V_{CC} = 3600V, I_C = 1000A, V_{GE} = ±15V, $R_{G(on)}$ = 4.3Ω, L_s = 150nH, Inductive load	T_j = 25°C	—	2.70	—	μs
			T_j = 125°C	—	3.30	—	
			T_j = 150°C	—	3.50	—	
I_{rr}	Reverse recovery current (Note 2)		T_j = 25°C	—	1130	—	A
			T_j = 125°C	—	1100	—	
			T_j = 150°C	—	1100	—	
$Q_{rr(10\%)}$	Reverse recovery charge (Note 2, 7)		T_j = 25°C	—	2200	—	μC
			T_j = 125°C	—	2750	—	
			T_j = 150°C	—	3000	—	
Q_{rr}	Reverse recovery charge (Note 2, 6)		T_j = 25°C	—	2250	—	μC
			T_j = 125°C	—	2800	—	
			T_j = 150°C	—	3100	—	
$E_{rec(10\%)}$	Reverse recovery energy (per pulse) (Note 2, 5)		T_j = 25°C	—	3.40	—	J
			T_j = 125°C	—	4.90	—	
			T_j = 150°C	—	5.50	—	
E_{rec}	Reverse recovery energy (per pulse) (Note 2, 6)		T_j = 25°C	—	3.60	—	J
			T_j = 125°C	—	5.10	—	
			T_j = 150°C	—	5.80	—	

THERMAL CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit
			Min	Typ	Max	
$R_{th(j-c)Q}$	Thermal resistance	Junction to Case, IGBT part	—	—	10.0	K/kW
$R_{th(j-c)D}$		Junction to Case, FWDi part	—	—	16.0	K/kW
$R_{th(c-s)}$	Contact thermal resistance	Case to heat sink, λ_{grease} = 1W/m·k, $D_{(c-s)}$ = 80μm	—	5.0	—	K/kW

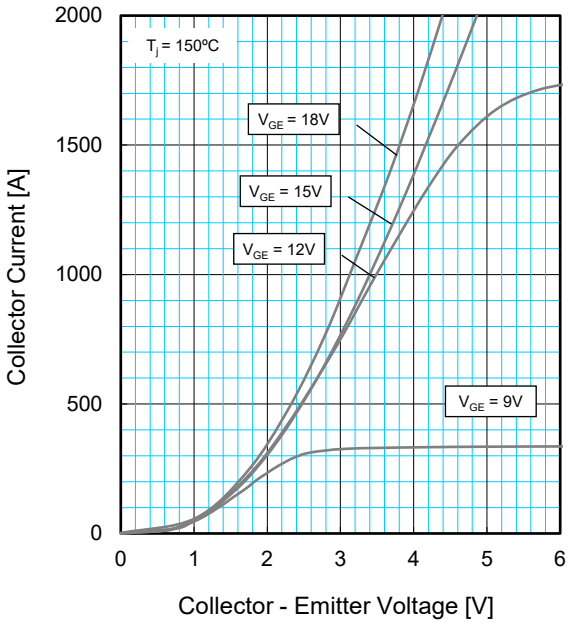
MECHANICAL CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit
			Min	Typ	Max	
M_t	Mounting torque	M8 : Main terminals screw	7.0	—	19.0	N·m
M_s		M6 : Mounting screw	3.0	—	6.0	N·m
M_t		M4 : Auxiliary terminals screw	1.0	—	3.0	N·m
m	Mass		—	1.5	—	kg
CTI	Comparative tracking index		600	—	—	—
d_a	Clearance		26.0	—	—	mm
d_s	Creepage distance		56.0	—	—	mm
$L_{P\ CE}$	Parasitic stray inductance		—	13.5	—	nH
$R_{CC'+EE'}$	Internal lead resistance	T_C = 25°C	—	0.12	—	mΩ

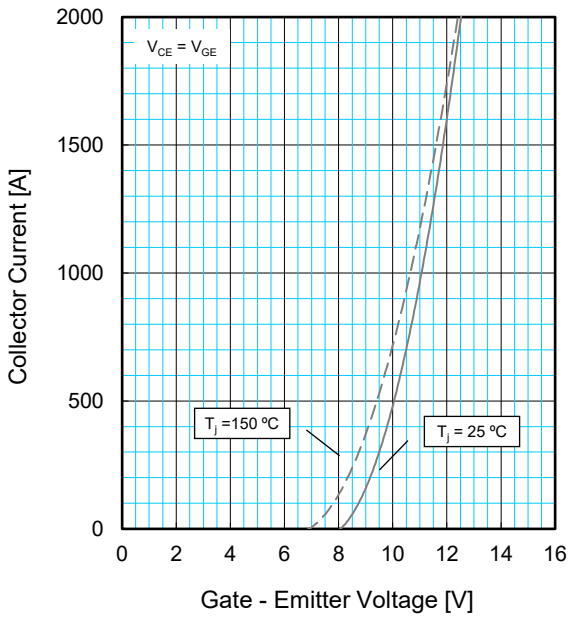
Note1. Pulse width and repetition rate should be such that junction temperature (T_j) does not exceed T_{jopmax} rating.
Note2. The symbols represent characteristics of the anti-parallel, emitter to collector free-wheel diode (FWD_i).
Note3. Junction temperature (T_j) should not exceed T_{jmax} rating (150°C).
Note4. Pulse width and repetition rate should be such as to cause negligible temperature rise.
Note5. The integration range of switching energies is from 10%V_{CE} to 10%I_C(10%I_E).
Note6. Definition of all items is according to IEC 60747, unless otherwise specified.
Note7. The integration range of reverse recovery charge is from I_E = 0A to 10%I_E.

PERFORMANCE CURVES

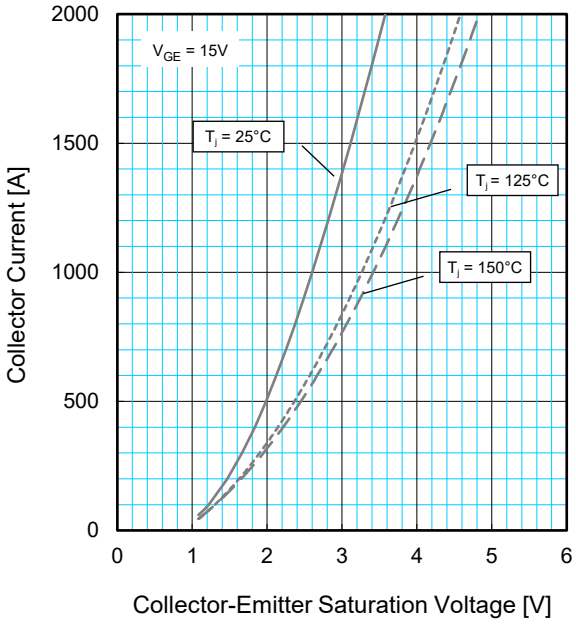
OUTPUT CHARACTERISTICS (TYPICAL)



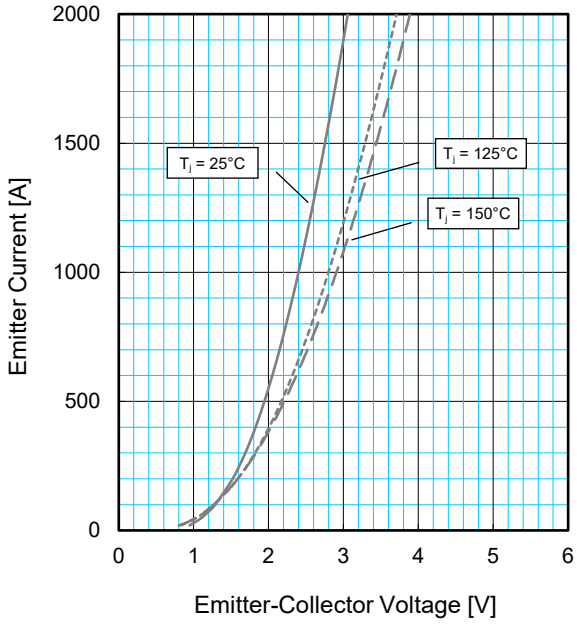
TRANSFER CHARACTERISTICS (TYPICAL)



COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)

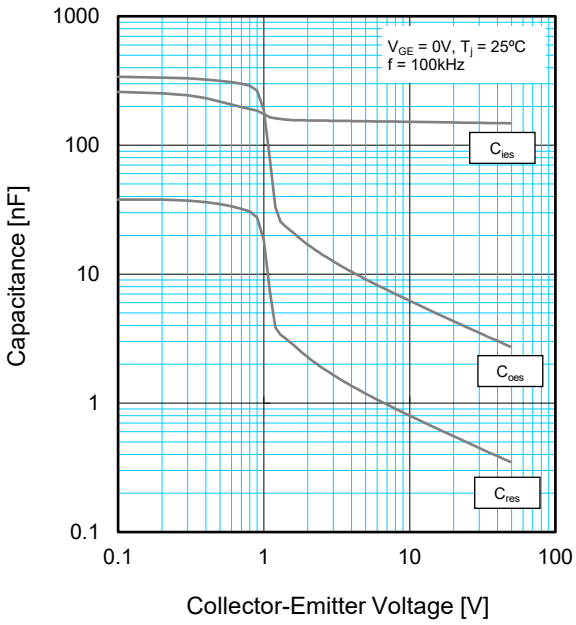


FREE-WHEEL DIODE FORWARD CHARACTERISTICS (TYPICAL)

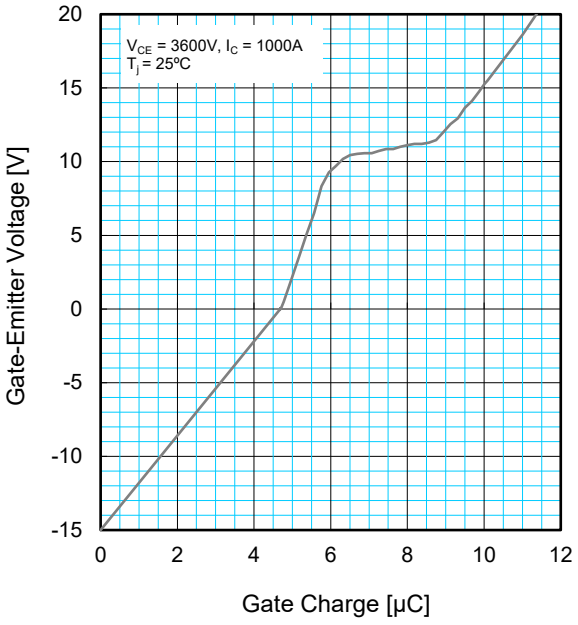


PERFORMANCE CURVES

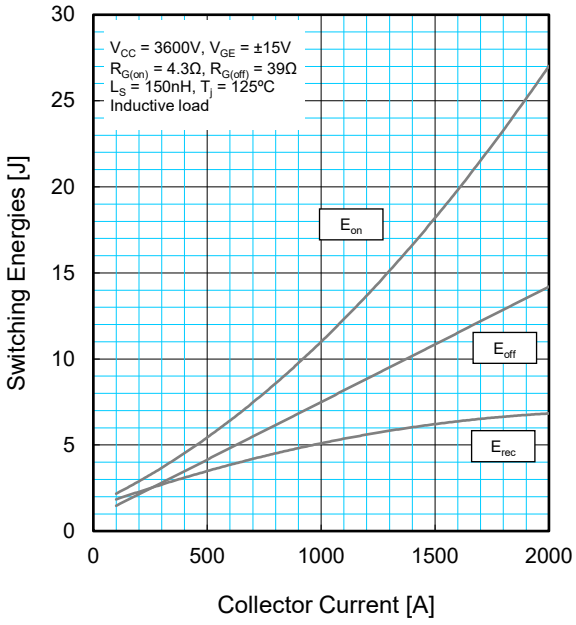
CAPACITANCE CHARACTERISTICS (TYPICAL)



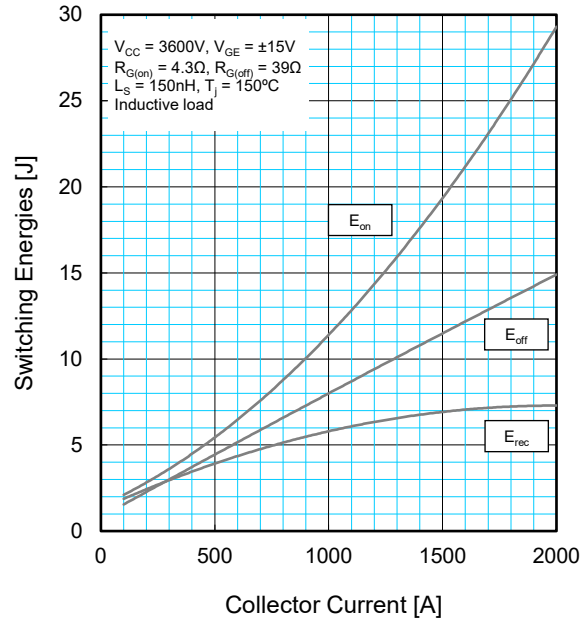
GATE CHARGE CHARACTERISTICS (TYPICAL)



HALF-BRIDGE SWITCHING ENERGY CHARACTERISTICS (TYPICAL)

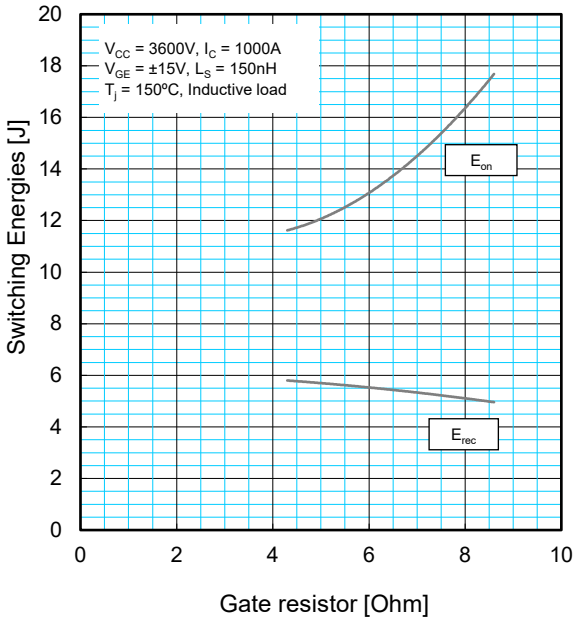


HALF-BRIDGE SWITCHING ENERGY CHARACTERISTICS (TYPICAL)

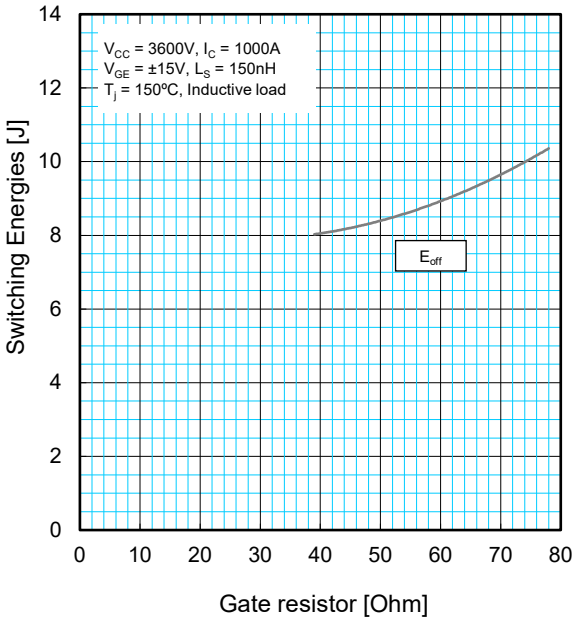


PERFORMANCE CURVES

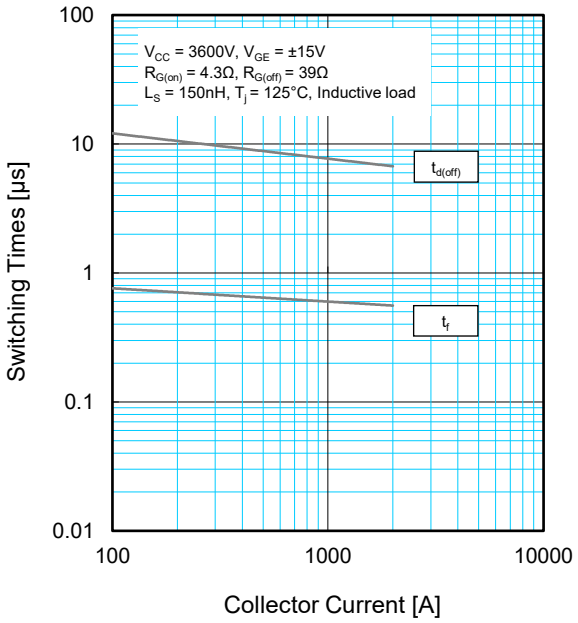
HALF-BRIDGE SWITCHING ENERGY CHARACTERISTICS (TYPICAL)



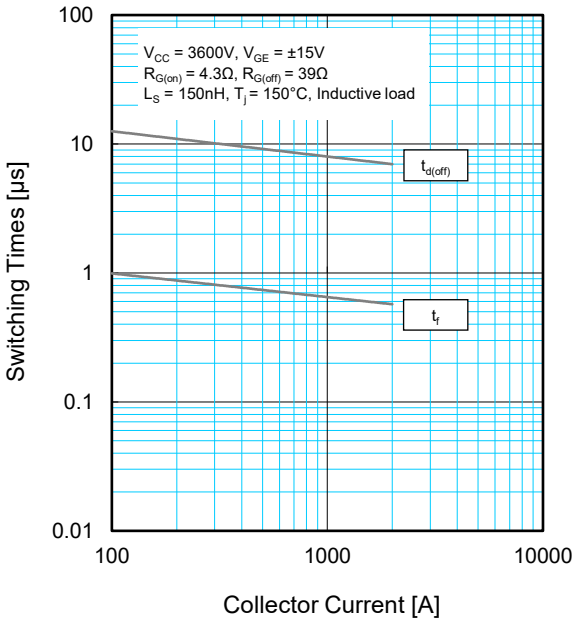
HALF-BRIDGE SWITCHING ENERGY CHARACTERISTICS (TYPICAL)



HALF-BRIDGE SWITCHING TIME CHARACTERISTICS (TYPICAL)

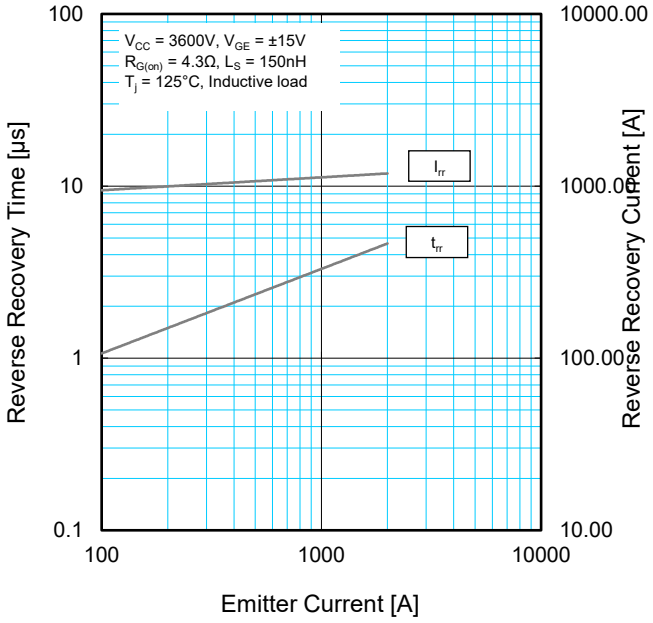


HALF-BRIDGE SWITCHING TIME CHARACTERISTICS (TYPICAL)

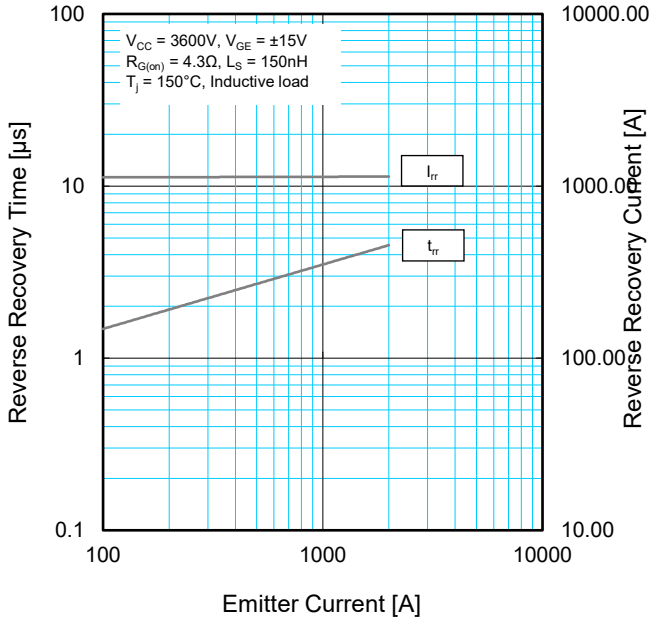


PERFORMANCE CURVES

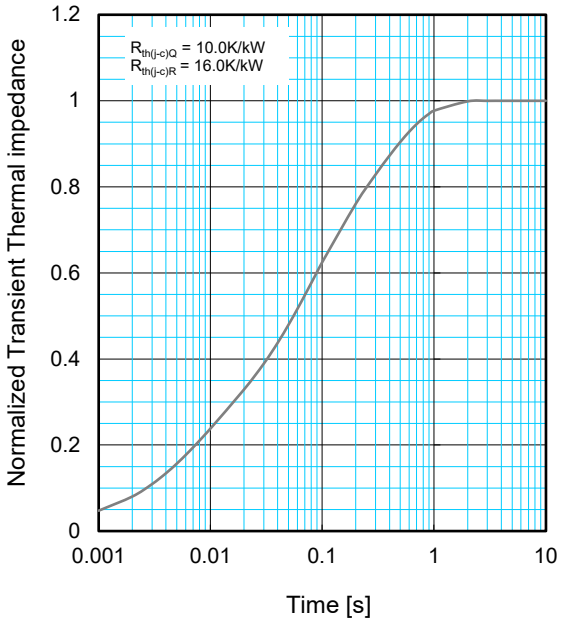
FREE-WHEEL DIODE REVERSE RECOVERY CHARACTERISTICS (TYPICAL)



FREE-WHEEL DIODE REVERSE RECOVERY CHARACTERISTICS (TYPICAL)



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS

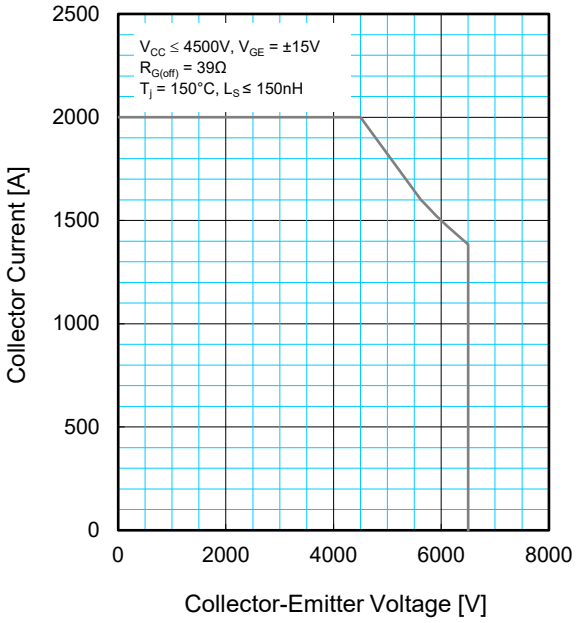


$$Z_{th(j-c)}(t) = \sum_{i=1}^{n} R_i \left\{ 1 - \exp\left(-\frac{t}{\tau_i} \right) \right\}$$

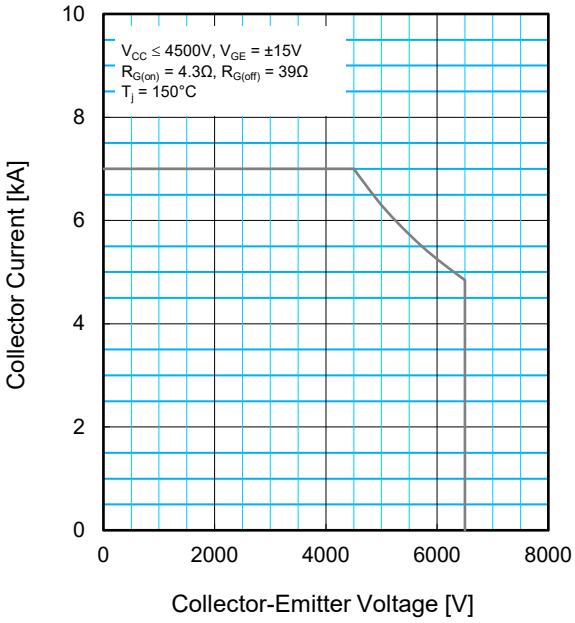
	1	2	3	4
R_i / $R_{th(j-c)}$:	0.0096	0.1893	0.4044	0.3967
τ_i [sec] :	0.0001	0.0058	0.0602	0.3512

PERFORMANCE CURVES

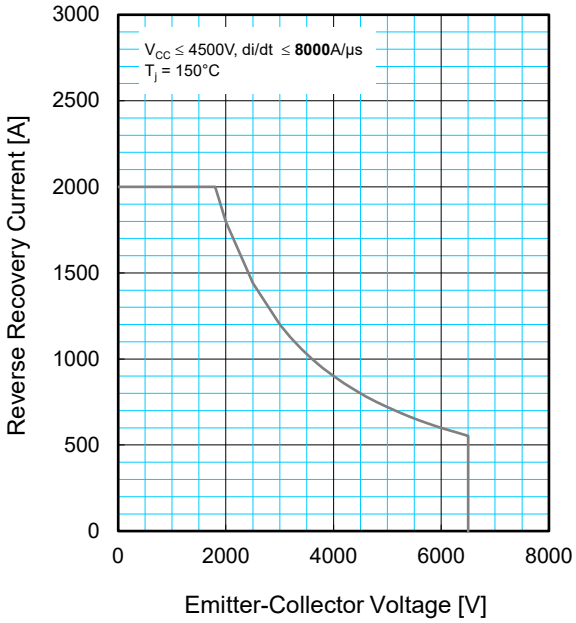
REVERSE BIAS SAFE OPERATING AREA (RBSOA)



SHORT CIRCUIT SAFE OPERATING AREA (SCSOA)



FREE-WHEEL DIODE REVERSE RECOVERY SAFE OPERATING AREA (RRSOA)



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